

ICDS Final Programme

as at 8 July 2011

Monday July 18th

0900 Welcome

0920 PLENARY TALK

Silicon Photovoltaics: Status, Defect Issues and the Emerging Role of Photoluminescence Imaging

Martin A Green, University of New South Wales, Sydney

1020 COFFEE

1050 Start of Parallel Sessions

Photovoltaics I	Theory
1050:Invited Talk	
Understanding defects in silicon photovoltaics by mechanical measurements	
<i>J Murphy, University of Oxford, UK</i>	
1130:PV1	1130:Th1
First-Principles Materials Design of CuInSe ₂ and Cu ₂ ZnSnSe ₄ -Based High Efficiency Solar Cells	Performance of various finite-size supercell correction schemes in charged defect calculations
<i>Y Tani, Osaka University, Japan</i>	<i>H Komsa, Ecole Polytechnique Federale de Lausanne, Switzerland</i>
1150:PV2	1150:Th3
Vacancy Studies in CuGaSe ₂ and CuInSe ₂ Thin Films	First principles study of O defects in CdSe
<i>E Korhonen, Aalto University, Finland</i>	<i>J T-Thienprasert, Kasetsart University, Thailand</i>
1210:PV3	1210:Th4
Modeling of incorporation of oxygen into multi-crystalline silicon during crystal growth	Effect of O-vacancy defects on the Schottky barrier heights in Ni/SiO ₂ and Ni/HfO ₂ interfaces
<i>Y Ohno, I Yonenaga, IMR, Tohoku University, Japan</i>	<i>H Noh, Korea Advanced Institute of Science and Technology, Korea</i>

LUNCH 1230-1350

Photovoltaics 2	Defects in SiC
1350: Invited talk	1350:SiC2
Properties of iron in silicon solar cells: recombination activity, gettering, and detection methods	Characterization of deep level defects in sublimation-grown p-type 6H-SiC epilayer by deep level transient spectroscopy
<i>D Macdonald, Australian National University, Australia</i>	<i>MA Hashmi, The Islamia University of Bahawalpur, Pakistan</i>
	1410:SiC3
	An Improved I-V model of 4H-SiC MESFETs with multiple deep level traps (DLT)
	<i>V L Narasimha Murty, Indian Institute of Technology – Bhubaneswar, India</i>
1430:PV4	1430:SiC4
Donor-Acceptor Pair Luminescence in Compensated Si for Solar Cells	Identification of Atomic Scale Defects in 4H SiC MOSFETs Using Electrically Detected Magnetic Resonance
<i>M Tajima, Institute of Space and Aeronautical Science/JAXA, Japan</i>	<i>C Cochrane, Pennsylvania State University, USA</i>
1450:PV5	
The study of below and above band-edge imperfection states in In ₂ S ₃ solar energy materials	
<i>C-H Ho, National Taiwan University of Science and Technology, Taiwan</i>	

Poster session 1

Tuesday 19th July

Defects in nanostructures	Defects in Germanium 1
0900: Invited talk	0900:Invited Talk
Defect and Crystal Phase Engineering of III-V Semiconductor Nanowires	First principles study of electronic and structural properties at the Ge/GeO ₂ interface
<i>J Wong-Leung, Australian National University, Australia</i>	<i>P Broqvist, École Polytechnique Fédérale de Lausanne, Switzerland</i>
0940:NS1	0940:Ge1
Impurity doping in semiconductor nanowires	Interfacial Conducting Layer at Ge _{1-y} Sny Grown on Si Substrate
<i>N Fukata, International Center for Materials Nanoarchitectonics, Japan</i>	<i>M Ryu, Kangwon National University, Korea</i>
1000:NS2	1000:Ge2
On the Focused Ion Beam Modification of Thin Si Lamellae	On the vacancy in germanium
<i>E Holmström, University of Helsinki and Helsinki Institute of Physics, Finland</i>	<i>S Kilpeläinen, Aalto University, Finland</i>

Coffee

Defects in Nitrides 1	Defects in Conducting Oxides 1
1050:Invited talk	1050: Invited talk
Evidence for dislocation atmospheres in the III-nitrides	Photoluminescence and exciton-phonon coupling in bulk ZnO
<i>S Moram, University of Cambridge, UK</i>	<i>R Reeves, University of Canterbury, New Zealand</i>
1130:N1	1130:CO1
Non-stoichiometric dislocations in GaN	Recombination activity of dislocations in wurtzite ZnO introduced at elevated temperatures
<i>B Hourahine, University of Strathclyde</i>	<i>Y Ohno, Institute for Materials Research, Tohoku University, Japan</i>
1150:N2	1150:CO2
Hexagonal (wurtzite) GaN inclusions as a defect in cubic (zinc-blende) GaN	Structural defect complexes versus impurity centers - Shallow and deep binding centers for excitons in ZnO and related materials
<i>N Zainal, Universiti Sains Malaysia, Malaysia</i>	<i>M Wagner, Technische Universität Berlin, Germany</i>
1210:N3	1210:CO3
Investigation of electron energy states in the InGa _N /Ga _N multiple quantum wells	Cross-sectional electron microscopy of IrO _x /ZnO Schottky diode interfaces
<i>MA Hashmi, The Islamia University of Bahawalpur, Pakistan</i>	<i>E Mayes, RMIT University, Melbourne, Australia</i>

LUNCH 1230-1350

Rare earths	Defects in Silicon 1
1350: Invited talk	1350:Invited Talk
Rare earth based compounds for photonic and photovoltaic applications,	Microdefects in germanium-doped Czochralski silicon
<i>Maria Miritello, University of Catania, Italy</i>	<i>Professor Deren Yang, Zhejiang University, China</i>
1430: RE1	1430:Si1
Enhancement of red emission in SrTiO ₃ :Pr ³⁺ by the addition of alliovalent cation -from the viewpoint of defect chemistry	Recombination at oxide precipitates in silicon
<i>Yoshiyuki Inaguma, Gakushuin University, Japan</i>	<i>J Murphy, University of Oxford, UK</i>
1450: RE2	1450:Si2
Determining the Structure of Rare-Earth Centres in GaN	Electronic Properties and Diffusivity of the Oxygen Dimer in Silicon
<i>B. Hourahine, University of Strathclyde</i>	<i>A R Peaker, University of Manchester, UK</i>

Poster session 2

Wednesday 20th July

Organic Semiconductors	Defects in Germanium 2
0850: Invited talk	0900:Ge3
Ion implantation effects on organic thin film transistors	Muonium Transitions in Ge-rich SiGe Alloys
<i>B.Fraboni, Università di Bologna, Italy</i>	<i>P Mengyan, Texas Tech University, USA</i>
0930:OS1	0920:Ge4
Origin and Characterization of Deep and Shallow Traps in Organic Molecular Semiconductors	The surface blistering kinetics and the H-platelet evolution in H-implanted germanium
<i>S Ghosh, Jawaharlal Nehru University, India</i>	<i>X Zhang, Institute of Microelectronics, Chinese Academy of Sciences, China</i>
0950: Invited talk	0940:Ge5
Electrically and Optically-Detected Electron Spin Resonance in PPV-based Organic Light Emitting Diodes	Oxygen in B ₂ O ₃ encapsulated Czochralski-grown Ge
<i>A Edgar, Victoria University, New Zealand</i>	<i>I Yonenaga, IMR, Tohoku University, Japan</i>
	1000:Ge6
	Positron Annihilation and Deep Level Transient Spectroscopy Studies of Vacancy-related Defects in Ion Implanted Germanium
	<i>J McCallum, University of Melbourne, Australia</i>

Coffee

Defects in Conducting Oxides 2	Defects in Si 2
1050:CO4	1045:Invited Talk
Dislocation levels acting as radiative recombination centers in compound semiconductors	Laplace Deep Level Transient Spectroscopy of Silicon ... Embodiment and Evolution
<i>Y Ohno, Institute for Materials Research, Tohoku University, Japan</i>	<i>A R Peaker, University of Manchester, UK</i>
1110:CO5	
Charge states of a hydrogen defect (3326 cm ⁻¹ line) in ZnO	
<i>E Lavrov, TU Dresden, IAP/Halbleiterphysik, Germany</i>	
1130:CO6	1130:Si3
Structural and optical characterization of indium and nitrogen codoped ZnO	Contamination of silicon by iron at low temperatures
<i>M Deicher, Universität des Saarlandes, Germany</i>	<i>J Murphy, University of Oxford, UK</i>
1150:CO7	1150:Si4
Motion of Positively-Charged Muonium in ZnO	On the impact of stress in intrinsic defect formation during single crystal silicon growth
<i>B Baker, Texas Tech University, USA</i>	<i>J Vanhellemont, Ghent University, Belgium</i>
	1210:Si5
	The CuPL defect and the Cu ₅ Cu ₁₃ complex
	<i>S Estreicher, Texas Tech University, USA</i>

Thursday 21th July

Defects in Compound Semiconductors	Defects in Conducting Oxides 3
0850:Invited talk	0900:CO9
Atomic and Electronic Structures of Defects at Interfaces and in Two-Dimensional Semiconductors	Metastable properties of a shallow-level defect in ZnO grown by pulsed laser deposition
<i>G Duscher, University of Tennessee (Knoxville), USA</i>	<i>F D Auret, University of Pretoria, South Africa</i>
0930:CS1	0920:CO10
Intrinsic defects in GaAs and InGaAs through hybrid functional calculations	IR absorption study of the VZnH2 defect in ZnO
<i>H Komsa, Ecole Polytechnique Federale de Lausanne, Switzerland</i>	<i>E Lavrov, TU Dresden, IAP/Halbleiterphysik, Germany</i>
0950:CS2	0940:CO11
Nanoscale Potential Fluctuations in (GaMn)As/GaAs Heterostructures: From Individual Ions to Charge Clusters and Electrostatic Quantum Dots	Monitoring Intrinsic Defects in Ion Implanted ZnO Using Li as a Tracer
<i>A Wijnheijmer, Eindhoven University of Technology, the Netherlands</i>	<i>P Neuvonen, University of Oslo, Norway</i>
1010:CS3	1000:CO12
Defect and Disorder in High Energy Light Ion Irradiated Undoped GaAs and GaAs:Cr	Muonium Dynamics in Transparent Conducting Oxides
<i>A Roy, Indian Institute of Technology Kharagpur, India</i>	<i>Y Celebi, Texas Tech University, USA</i>

Coffee

Nitrides 2	Defects in Conducting Oxides 4
1050:N4	1050:CO13
Structural and local electrical properties of AlInN/AlN/GaN heterostructures	The role of intrinsic gap states and native defects at ZnO surfaces and interfaces
<i>A Cavallini, University of Bologna, Italy</i>	<i>M Allen, University of Canterbury, New Zealand</i>
1110:N5	1110:CO14
Structural defect anisotropy of PVT grown AlN (1-102) single crystals	Phase Diagrams of polar Surface Reconstructions of Zinc Oxide
<i>L Kirste, Fraunhofer Institute of Applied Solid State Physics, Germany</i>	<i>M Gluba, Helmholtz-Zentrum Berlin für Materialien und Energie, Germany</i>
1130:N6	1130:CO15
Defect studies in In-rich III-Nitrides with positron annihilation spectroscopy	Hydrogen shallow donor in rutile TiO ₂
<i>C Rauch, Aalto University, Finland</i>	<i>Herklotz F, TU Dresden, IAP/Halbleiterphysik, Germany</i>
1150:N7	
Local Conduction Paths in Nitride-based heterostructure	
<i>A Minj, University of Bologna, Italy</i>	

LUNCH 1230-1350

Defects in Si 3

1350: Invited talk

Symmetry and structure of N-O shallow donor complexes in silicon

Hans Ch. Alt, Munich University of Applied Sciences, Germany

1430:Si6

300 mm Czochralski Silicon Wafers Optimized with Respect to Voids with Laterally Homogeneous Internal Getter Capabilities

G Kissinger, IHP, Germany

Poster session 3

Friday 22nd July

Defects in Magnetic Semiconductors 1	Defects in Si 4
	0900:Si8
	Deep Level Transient Spectroscopy study of ion implantation-induced extended defects in silicon
	<i>J Boucher, LAAS-CNRS, France</i>
0920:Invited Talk	0920:Si9
Phase separation in magnetic semiconductors: Coherent aggregation of magnetic ions vs. precipitation of magnetic nanoclusters	Impact of radiation induced bulk defects on electrical properties of silicon sensors for the HL-LHC
<i>S Kuroda, University of Tsukuba, Japan</i>	<i>A Junkes, Hamburg University, Germany</i>
	0940:Si10
	Raman investigation of ro-vibrational modes of interstitial H ₂ in Si
	<i>E Lavrov, TU Dresden, Germany</i>
1000:MS1	1000:Si11
First-Principles Study of the Magnetic Properties of Nitrogen-doped Alkaline Earth Metal Oxides	Effect of Dopants on the Photoluminescence of Interstitial-related Defect Centres in Ion Implanted Silicon
<i>M Seike, Osaka University, Japan</i>	<i>J McCallum, University of Melbourne, Australia</i>

Coffee

Defects in Magnetic Semiconductors 2	Defects in Si 5
1050:MS3	1050:Si12
Defect annealing in Mn/Fe implanted ZnO	Vacancy formation energy in Cz-Si crystals determined by a quenching method
<i>D Naidoo, School of Physics, University of the Witwatersrand, South Africa</i>	<i>I Yonenaga, Tohoku University, Japan</i>
1110:MS4	1130:Si14
Rare-earth nitrides; intrinsic ferromagnetic semiconductors	Precipitation in Silicon Wafers after High Temperature Preanneal Studied by X-ray Diffraction Methods
<i>B Ruck, MacDiarmid Institute, Victoria University, New Zealand</i>	<i>M Meduna, Masaryk University, Czech Republic</i>
1130:MS5	1110:Si13
Computational Materials Design of Filled Tetrahedral Compound Magnetic Semiconductors	Time Delayed Mössbauer Measurements on Si single-crystals
<i>K Sato, Osaka University, Japan</i>	<i>D Naidoo, University of the Witwatersrand, South Africa</i>

End of conference

Poster session 1 Monday afternoon

Photovoltaics

- PPV.1: Evaluating Effect of Surface State Density at the Interfaces in Degraded Bulk Heterojunction Organic Solar Cell
S Arora, Zakir Husain College, University of Delhi, India
- PPV.2: Photoelectrochemical Studies on Chemically Grown CdSe : Sb Thin Film Electrodes
E Masumdar, Rrajarsi Shahu Mahavidyalaya, Latur, India
- PPV.3: Characterization of Al/Cu₃BiS₃/Buffer/ZnO Solar Cells Structure by TEM
F Mesa, Universidad Nacional de Colombia, Universidad Libre, Colombia
- PPV.4: The effect of efficiency in inverted organic solar cell by thickness of ZnO electron transport layer
W Jang, School of Advanced Materials Science and Engineering, Sungkyunkwan University, Republic of Korea
- PPV.5: Temperature dependence of linear thermal expansion of I-III-VI₂ single crystal
A Nagaoka, University of Miyazaki, Japan
- PPV.6: Optical and Electrical Characterization of ZnO Thin Films Grown by Atmospheric Spray Pyrolysis
K Naomi, Department of Electrical and Electronic Engineering, University of Miyazaki, Japan
- PPV.7: Electronic structure of tin dioxide using first principles calculations
M Oshima, University of Miyazaki, Japan
- PPV.8: Hybrid solar cells with p-type conducting polymer and vertically aligned n-Si nanorod: the effects of Si conductivity
S Woo, Daegu Gyeongbuk Institute of Science and Technology (DGIST), Kyungpook National University, Korea

Theory

- PTh.1: First principles study of Mg-doped ZnO
N Palakawong, School of Physics, Suranaree University of Technology and Synchrotron Light Research Institute, Nakhon Ratchasima 30000, Thailand, Thailand Center of Excellence in Physics (ThEP Center), Commission on Higher Education, Bangkok 10400, Thailand
- PTh.2: First-principles study of the segregation of boron dopants in Si/SiO₂ interface
Y Oh, Department of Physics, Korea Advanced Institute of Science and Technology, Korea
- PTh.3: Theoretical Study of Band Gap in CuAlO₂: Pressure Dependence and Self-Interaction Correction
A Nakanishi, Osaka University, Japan

Silicon Carbide

- PSiC.1: Study of deep level defects in doped and semi-insulating n-6H-SiC epilayers grown by sublimation method
M Asghar, The Islamia University of Bahawalpur, Pakistan

Nanostructures 1

- PNS.1: Low-frequency Noise Behavior of Strained-Si/SiGe n-MOSFETs
C Mukherjee, Department of Electronics & Electrical Communication Engineering, Indian Institute of Technology, Kharagpur, India
- PNS.2: Defect-effects on the photoluminescence of ZrO₂ bulk, film and nanocrystals
S Mochizuki, Nihon University, Japan
- PNS.3: Fabrication and electrical properties of P doped ZnO nanorods by magnetron sputtering
Y Kim, School of Advanced Materials Science & Engineering, Sungkyunkwan University, Korea
- PNS.4: Nanoscale Order in ZnS:(O,Cd)
S Díaz, ESIME-IPN Culhucan, Av. Sta. Ana 1000, Mexico
- PNS.5: Decomposition and Unstable States of ZnTeS and CdZnTeS Alloys
S Díaz, ESIME-IPN Culhucan, Av. Sta. Ana 1000, Mexico

Diamond

- PD.1: Giant concentration of nitrogen-vacancy defects in sintered detonation nanodiamonds
A Soltamova, Ioffe Physical-Technical Institute, Russia
- PD.2: Optical Properties of the Neutral Silicon Split-Vacancy Centre in Diamond
B Green, University of Warwick, United Kingdom
- PD.3: Uniaxial Stress Splitting Studies of the 490.8 nm and 648 nm Systems in Diamond
B Green, University of Warwick, United Kingdom
- PD.4: Irradiated diamond spectra (GR-1 band)
K Boris, 1 St.-Petersburg State Medical University, Russia
- PD.5: Mössbauer measurements on ion-implanted Sb/Sn in diamond
K Bharuth-Ram, University of KwaZulu-Natal, South Africa

Poster session 2 Tuesday afternoon

Rare Earths

- PRE.1: Schottky barriers based on metal nanoparticles deposited onto high-purity InP layers prepared from rare-earth treated liquid phase
J Grym, Institute of Photonics and Electronics, Academy of Sciences, Czech Republic
- PRE.2: Effect of Co-doping Content on Hydrothermal Derived ZnO Array Films
X He, South China University of Technology, China

Germanium

- PGe.1: Stability of Valence Alternation Pairs across the Substoichiometric Region at Ge/GeO₂ Interfaces
J Binder, École polytechnique fédérale de Lausanne (EPFL), Switzerland
- PGe.2: On the Concentration Dependence of N-type Dopant Diffusion and Activation in Si and Ge
J Vanhellemont, Dept. of Solid State Sciences, Ghent University, Belgium
- PGe.3: Characterization of electrically active defects introduced in n-Ge by hydrogen passivation
C Nyamhere, Department of Physics, Nelson Mandela Metropolitan University, PO Box 77000, Port Elizabeth 6031, South Africa
- PGe.4: Doping effects for dislocation motion in Ge
Y Murao, Institute for Materials Research, Tohoku University, Japan

Nitrides

- PN.1: Microstructure of Nonpolar GaN Grown at Low-temperature
Y Tokumoto, Institute for Materials Research, Tohoku University, Japan
- PN.2: Surface roughness scattering limited 2DEG mobility in InAlN/AlN/GaN heterostructures
S Pandey, University of Bologna, Italy
- PN.3: Electronic and magnetic properties of GaInN solid solution with manganese and hydrogen impurities
S Syrotyuk, National University Lviv Polytechnic, Ukraine
- PN.4: Charge Carrier Scattering on the Short-range Potential of the Crystal Defects in Gallium Nitride
O Malyk, Lviv Polytechnic National University, Semiconductor Electronics Department
- PN.5: EPR investigations of donor centers in AlN
A Soltamova, Ioffe Physical-Technical Institute, Russia
- PN.6: Hydrogen Interaction with GaN Metal-Insulator-Semiconductor Diodes
Y Irokawa, National Institute for Materials Science, Japan
- PN.7: Characterisation of Defects in p-GaN by Admittance Spectroscopy
K Vernon-Parry, MERI, Sheffield Hallam University, United Kingdom

Nanostructures 2

- PNS.8: Structural characterizations of sol-gel synthesized TiO₂ and Ce/TiO₂ nanostructures
A Niltharach, Kasetsart University, Thailand
- PNS.9: Novel 8x8 Field-Emission Transistor Arrays Based Single-Walled Carbon Nanotubes for Selectively Detection
K Kim, Korea Institute of Science and Technology, Korea
- PNS.10: UV-laser-light-cotrolled photoluminescence of metal oxide nanostructures in different atmospheres
S Mochizuki, Nihon University, Japan
- PNS.11: Theoretical study of single-walled carbon nanotubes functionalized with MEH-PPV residues: A DFT calculation
P Prajongtat, Department of Chemistry, Faculty of Science, Kasetsart University, Center of Nanotechnology KU, and NANOTEC Center of Excellence at Kasetsart University, Kasetsart University, Jatuchak, Bangkok, Thailand
- PNS.12: Properties of InAs/AIAs heterostructures
V Marushak, St.-Petersburg State Medical University, 6/8 Leo Tolstoy st., St.-Petersbug 197022, Russia
- PNS.13: Test challenges in analog Nano-CMOS technology
M Karmani, Electronics & Microelectronics Laboratory, Monastir, Tunisia

Organic semiconductors

- POS.1: Dipole-Charge Carrier Interaction as a Source of Artificial Traps in Organic Field Effect Transistors (OFETs)
B Paez-Sierra, Thin films group, Physics department, Pontificia Universidad Javeriana, Colombia

Conducting Oxides

- PCO.1: Gate bias and illumination stability of Al-doped ZnO thin-film-transistors
C Ahn, School of Advanced Materials Science and Engineering, Sungkyunkwan University, Korea
- PCO.2: Influence of Annealing on UV photodetection property of Indium Zinc Oxide film
K Kim, Green Energy Research Division, Daegu-Gyeongbuk Institute of Science and Technology (DGIST), Korea
- PCO.3: Investigation of Si doping effect into b-Ga₂O₃ film by co-sputtering of gallium oxide and Si
K Takakura, Kumamoto National College of Technology, Japan
- PCO.4: Properties and identification of bound excitons in ZnO
K Johnston, CERN, CH-1211 Geneva 23, Switzerland, University of Saarlandes, 66123 Saarbrücken, Germany
- PCO.5: The local environment of indium in In₂O₃(ZnO)_m and indium doped ZnO studied with perturbed angular correlation
P Kessler, Helmholtz - Institut für Strahlen- und Kernphysik, 53115 Bonn, Germany
- PCO.5: Device quality ZnO grown using a Filtered Cathodic Vacuum Arc
S Elzwawi

Poster session 3 Thursday afternoon

Silicon

- PSi.1: Effect of impurities on the thermal stability of tensile strain in solid phase epitaxial regrowth formed Si:C alloy
W Woon, National Central University, Taiwan
- PSi.2: Electronic properties of dislocations introduced mechanically at room temperature on single crystal silicon surface
M Ogawa, Nagoya Institute of Technology, Japan
- PSi.3: Thermal evolution of surface blistering and exfoliation due to ion-implanted hydrogen monomers into Si<111>
J Liang, National Tsing Hua University, Taiwan
- PSi.4: Dissolution of dislocation cores by chemical etching – application to multicrystalline silicon
J D Murpy, Department of Materials, University of Oxford, UK
- PSi.5: Interaction of dopant atoms with stacking faults in Si
Y Ohno, Institute for Materials Research, Tohoku University, Japan
- PSi.6: Grown-in defects in CZ-Si heavily doped with B atoms
Y Ohno, Institute for Materials Research, Tohoku University, Japan
- PSi.7: Dislocation luminescence in electron beam treated silicon
L Xiang, State Key Laboratory of Silicon Materials and Department of Materials Science and Engineering, Zhejiang University, People's Republic of China
- PSi.8: Study of Irradiation Induced Changes of Electrical and Functional Characteristics in Ge Doped Si Diodes
J Vanhellemont, Dept. of Solid State Sciences, Ghent University, Belgium
- PSi.9: Three C Pairs in Si and their Interactions with H
S Estreicher, Texas Tech University, United States
- PSi.10: Computational Approaches for Evaluation of Atomic Displacement Damage Using Monte Carlo Method
H Daneshvar, Shahid Beheshti University, Iran
- PSi.11: Defects Engineering for Silicon Power Diode by X-ray Irradiation
P Rujanapich, Faculty of Engineering, King Mongkut's Institute of Technology Ladkrabang, Thailand
- PSi.12: Non-uniform Defects Assessment by I-V and C-V characteristics of p-n junction
W Pengchan, King Mongkut's Institute of Technology Ladkrabang, Thailand
- PSi.13: NBTI Degradation Effect in Thin and Thick Effective Oxide Thickness (EOT) p-MOSFET Devices
H Hussin, Faculty of Electrical Engineering, Universiti Teknologi MARA, Malaysia
- PSi.14: Reconfigurations and Diffusion of Small Vacancy Clusters in Silicon
A R Peaker, University of Manchester, Manchester, United Kingdom
- PSi.15: Phonon assisted photoluminescence properties of Si nanocrystals from 50 keV Ar ion induced rippled Si (100)
T Kumar, Inter-University Accelerator Centre, Aruna Asaf Ali Marg, New Delhi-110067, India
- PSi.16: Diode Characteristics and Thermal Donor Formation in Germanium-doped Silicon Substrates
J Vanhellemont, Dept. of Solid State Sciences, Ghent University, Belgium

Compound Semiconductors

- PCS.1: Defect detection by cathodoluminescence in semiconductor layers with built-in electric field
M Pluska, Institute of Electron Technology, Japan
- PCS.2: Transients Electron Trapping Phenomenon in P-N Junction Diode Fabricated in High Energy Boron Implanted.
I Srithanachai, King Mongkut's Institute of Technology Ladkrabang, Thailand
- PCS.3: Characterization of CuInGaSe₂ films on Mo substrate by RF sputtering
K Yoshino, University of Miyazaki, Japan
- PCS.4: On the Validity of Diffusional Model in Determination Electric Transport Parameters on Compound Semiconductors
F Mesa, Departamento de Ciencias Basicas, Universidad Libre, Bogota-Colombia, Departamento de Fisica, Universidad Nacional de Colombia, Bogota-Colombia, Colombia
- PCS.5: Characterization of AgInS₂ Thin Films Prepared by Vacuum Evaporation
Y Akaki, Miyakonojo National College of Technology, Japan
- PCS.6: Epitaxial growth on porous III-V semiconductors
J Grym, Institute of Photonics and Electronics, Academy of Sciences, Czech Republic
- PCS.7: Excitonic insulator phase in indium antimonide doped with manganese
S Obukhov, A.F.Ioffe Institute of Physics & Technology, Russia
- PCS.8: Optical Characterization of GaTe layered crystal Grown by Bridgman Method
M Yoneta, Okayama University of Science, Japan
- PCS9: X-ray Radiation Damage in P-N Junction Diode
I Srithanachai, King Monkut's Institute of Technology Ladkrabang, Thailand
- PCS.10 Characterization of Cu₂ZnSn(S, Se)₄ Single Crystal by Traveling Heater Method
A. Nagaoka, University of Miyazaki, Japan

Magnetic Semiconductors

- PMS.1: Room temperature GdN thin films: Resistivity and magnetization
N Plank, School of Chemical and Physical Sciences, Victoria University of Wellington, New Zealand
- PMS.2: The interstitial codoping method for increasing the solubility of magnetic impurities in DMS
H Fujii, Graduate School of Engineering Science, Osaka University, Japan
- PMS.3: Study of ferromagnetism in cobalt-doped ZnO diluted magnetic semiconductor
D Seghier, Science Institute, University of Iceland